

GaAs-IR-Lumineszenzdiode
GaAs Infrared Emitter
Lead (Pb) Free Product - RoHS Compliant

LD 274



Wesentliche Merkmale

- GaAs-LED mit sehr hohem Wirkungsgrad
- Hohe Zuverlässigkeit
- Gute spektrale Anpassung an Si-Fotoempfänger
- Gehäusegleich mit SFH 484

Features

- Very highly efficient GaAs-LED
- High reliability
- Spectral match with silicon photodetectors
- Same package as SFH 484

Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern
- Gerätefernsteuerungen für Gleich- und Wechsellichtbetrieb
- Sensorik
- Diskrete Lichtschranken

Applications

- IR remote control of hi-fi and TV-sets, video tape recorders, dimmers
- Remote control for steady and varying intensity
- Sensor technology
- Discrete interrupters

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
LD 274	Q62703Q1031	5-mm-LED-Gehäuse (T 1 ³ / ₄), graugetöntes Epoxy-Gießharz, Anschlüsse im 2.54-mm-Raster (¹ / ₁₀ "), Kathodenkennzeichnung: Kürzerer Lötspieß, flat 5 mm LED package (T 1 ³ / ₄), grey colored epoxy resin lens, solder tabs lead spacing 2.54 mm (¹ / ₁₀ "), cathode marking: shorter solder lead, flat
LD 274-2 ¹⁾	Q62703Q1819	
LD 274-3	Q62703Q1820	

¹⁾ Nur auf Anfrage lieferbar.

¹⁾ Available only on request.

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Durchlassstrom Forward current	I_F	100	mA
Stoßstrom, $t_p = 10\text{ }\mu\text{s}$, $D = 0$ Surge current	I_{FSM}	3	A
Verlustleistung Power dissipation	P_{tot}	165	mW
Wärmewiderstand Thermal resistance	R_{thJA}	450	K/W

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	λ_{peak}	950	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	$\Delta\lambda$	55	nm
Abstrahlwinkel Half angle	φ	± 10	Grad
Aktive Chipfläche Active chip area	A	0.09	mm ²
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm ²
Abstand Chipoberfläche bis Linsenscheitel Distance chip front to lens top	H	4.9 ... 5.5	mm
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$	t_r , t_f	0.5	μs

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics** (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Kapazität Capacitance $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_0	25	pF
Durchlassspannung Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F V_F	1.30 (≤ 1.5) 1.90 (≤ 2.5)	V V
Sperrstrom, $V_R = 5\text{ V}$ Reverse current	I_R	0.01 (≤ 1)	μA
Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	Φ_e	20	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.55	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 1.5	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	+ 0.3	nm/K

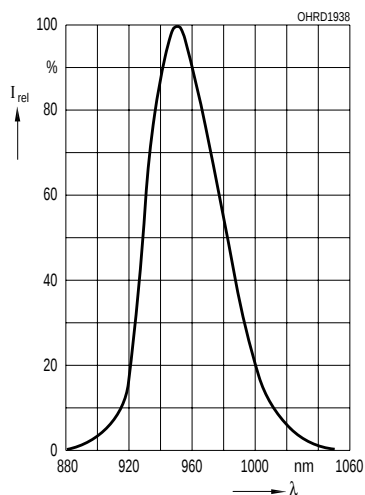
Gruppierung der Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.001$ sr**Grouping of Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.001$ sr

Bezeichnung Parameter	Symbol Symbol	Wert Value			Einheit Unit
		LD 274	LD 274-2 ¹⁾	LD 274-3	
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \text{ min}}$ $I_{e \text{ max}}$	50 –	50 100	80 –	mW/sr mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e \text{ typ.}}$	700	600	800	mW/sr

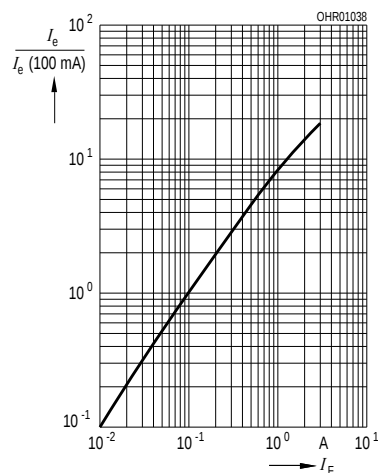
¹⁾ Nur auf Anfrage lieferbar.¹⁾ Available only on request.

Relative Spectral Emission

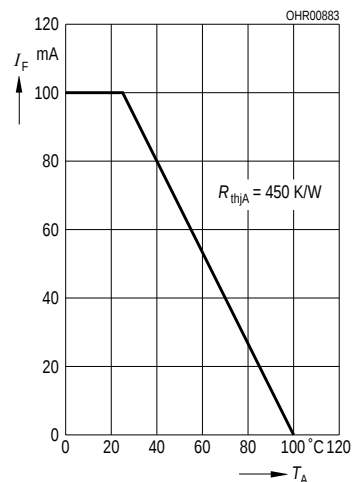
$$I_{\text{rel}} = f(\lambda)$$



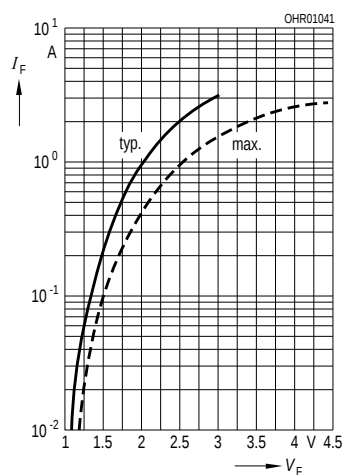
$$\text{Radiant Intensity } \frac{I_e}{I_e \text{ 100 mA}} = f(I_F)$$

Single pulse, $t_p = 20 \mu\text{s}$ **Max. Permissible Forward Current**

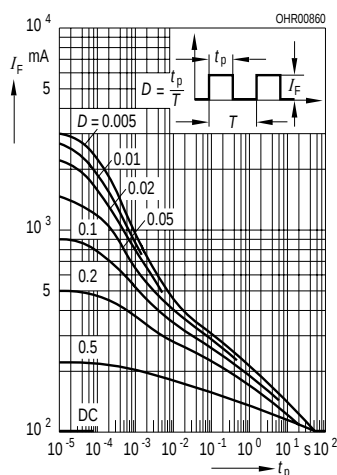
$$I_F = f(T_A)$$

**Forward Current**

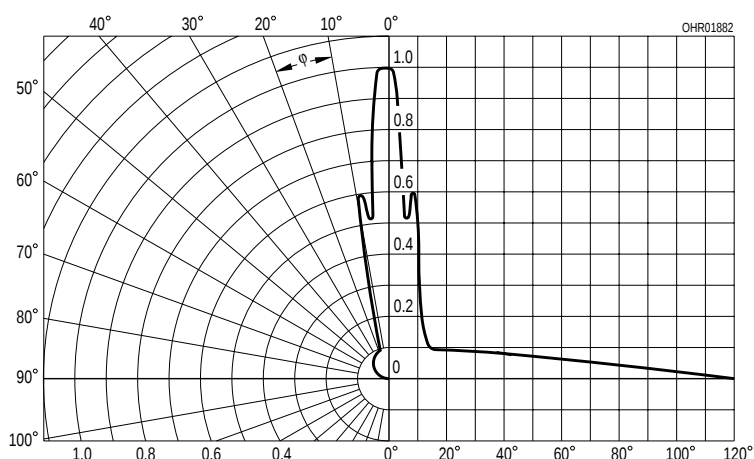
$$I_F = f(V_F), \text{ single pulse, } t_p = 20 \mu\text{s}$$

**Permissible Pulse Handling**

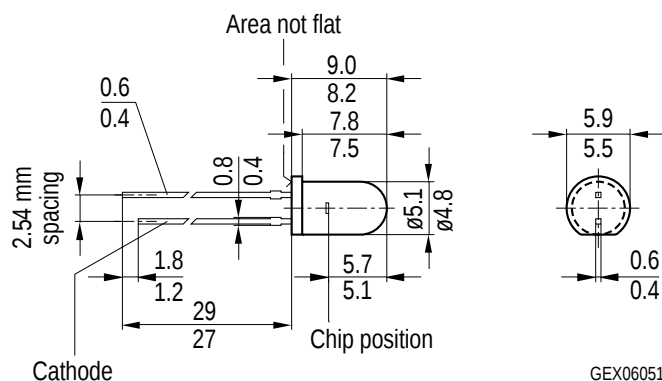
$$\text{Capability } I_F = f(\tau), T_C \leq 25^\circ\text{C}, \text{ duty cycle } D = \text{parameter}$$

**Radiation Characteristics,**

$$I_{\text{rel}} = f(\varphi)$$



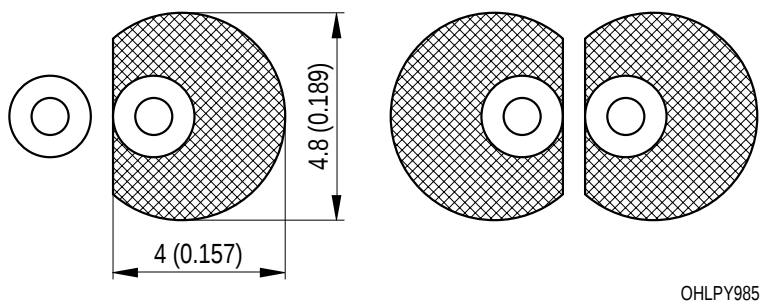
Maßzeichnung Package Outlines



Maße in mm (inch) / Dimensions in mm (inch).

Empfohlenes Lötpaddesign Recommended Solder Pad

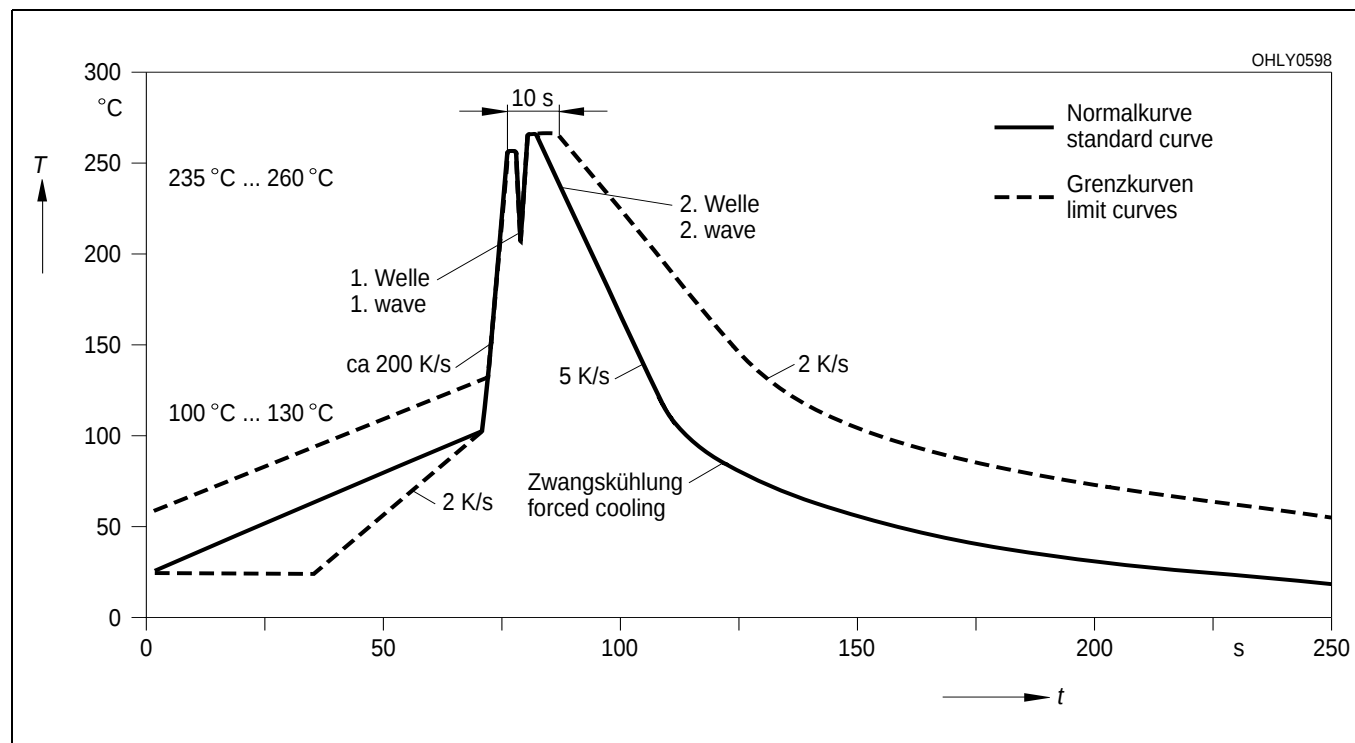
Wellenlöten (TTW) TTW Soldering



Maße in mm (inch) / Dimensions in mm (inch).

Lötbedingungen
Soldering Conditions
Wellenlöten (TTW)
TTW Soldering

(nach CECC 00802)
 (acc. to CECC 00802)



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